UNR3111

Silicon PNP epitaxial planar type

For digital circuits

■ Features

- Suitable for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V _{CBO} | -50 | V | |
| Collector-emitter voltage (Base open) | V _{CEO} | -50 | V | |
| Collector current | $I_{\rm C}$ | -100 | mA | |
| Total power dissipation | P_{T} | 100 | mW | |
| Junction temperature | T _j | 125 | °C | |
| Storage temperature | T _{stg} | -55 to +125 | °C | |

Package

- Code
- SSSMini3-F1
- Pin Name
 - 1: Base
 - 2: Emitter
 - 3: Collector

■ Marking Symbol: 6A

■ Internal Connection

$$\begin{array}{c|c} R_1 & (10 \text{ k}\Omega) \\ B \circ & W & C \\ R_2 & (10 \text{ k}\Omega) & F \end{array}$$

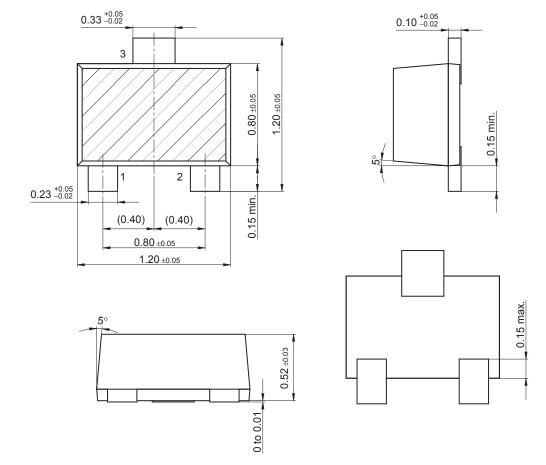
■ Electrical Characteristics $T_a = 25$ °C±3°C

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|--|------|-----|-------|------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_{\rm C} = -10 \mu \text{A}, I_{\rm E} = 0$ | -50 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$ | -50 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = -50 \text{ V}, I_{E} = 0$ | | | -0.1 | μΑ |
| Collector-emitter cutoff current (Base open) | I _{CEO} | $V_{CE} = -50 \text{ V}, I_{B} = 0$ | | | -0.5 | μΑ |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = -6 \text{ V}, I_C = 0$ | | | -0.5 | mA |
| Forward current transfer ratio | h_{FE} | $V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$ | 35 | | | _ |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$ | | | -0.25 | V |
| Output voltage high-level | V _{OH} | $V_{CC} = -5 \text{ V}, V_{B} = -0.5 \text{ V}, R_{L} = 1 \text{ k}\Omega$ | -4.9 | | | V |
| Output voltage low-level | V _{OL} | $V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | | | -0.2 | V |
| Input resistance | R_1 | | -30% | 10 | +30% | kΩ |
| Resistance ratio | R_1/R_2 | | 0.8 | 1.0 | 1.2 | _ |
| Transition frequency | f_T | $V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$ | | 80 | | MHz |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

SSSMini3-F1

Unit: mm



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